Inverter Grade Thyristors (Hockey PUK Version), 720 A



TO-200AB (E-PUK)

FEATURES

- Metal case with ceramic insulator
- All diffused design
- Center amplifying gate
- Guaranteed high dV/dt
- Guaranteed high dI/dt
- International standard case TO-200AB (E-PUK)
- High surge current capability
- Low thermal impedance
- High speed performance
- Lead (Pb)-free

Pb-free
RoHS COMPLIANT

PRODUCT SUMMARY	
$I_{T(AV)}$	720 A

TYPICAL APPLICATIONS

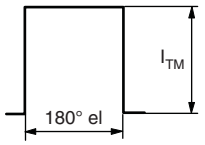
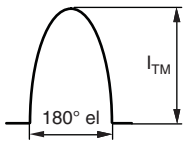
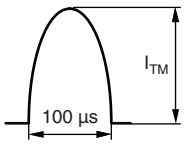
- Inverters
- Choppers
- Induction heating
- All types of force-commutated converters

MAJOR RATINGS AND CHARACTERISTICS			
PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$		720	A
	T_{hs}	55	°C
$I_{T(RMS)}$		1435	A
	T_{hs}	25	°C
I_{TSM}	50 Hz	11 000	A
	60 Hz	11 500	
I^2t	50 Hz	605	kA^2s
	60 Hz	553	
V_{DRM}/V_{RRM}		400 to 800	V
t_q	Range	10 to 30	µs
T_J		- 40 to 125	°C

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS				
TYPE NUMBER	VOLTAGE CODE	V_{DRM}/V_{RRM}, MAXIMUM REPETITIVE PEAK VOLTAGE V	V_{RSM}, MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA
ST333C..C	04	400	500	50
	08	800	900	

CURRENT CARRYING CAPABILITY

FREQUENCY							UNITS
50 Hz	1630	1420	2520	2260	7610	6820	A
400 Hz	1630	1390	2670	2330	4080	3600	
1000 Hz	1350	1090	2440	2120	2420	2100	
2500 Hz	720	550	1450	1220	1230	1027	
Recovery voltage V_r	50		50		50		V
Voltage before turn-on V_d	V_{DRM}		V_{DRM}		V_{DRM}		
Rise of on-state current dI/dt	50		-		-		A/µs
Heatsink temperature	40	55	40	55	40	55	°C
Equivalent values for RC circuit	10/0.47		10/0.47		10/0.47		Ω/µF

ON-STATE CONDUCTION

PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current at heatsink temperature	$I_{T(AV)}$	180° conduction, half sine wave Double side (single side) cooled			720 (350)	A
					55 (75)	°C
Maximum RMS on-state current	$I_{T(RMS)}$	DC at 25 °C heatsink temperature double side cooled			1435	A
Maximum peak, one half cycle, non-repetitive surge current	I_{TSM}	t = 10 ms	No voltage reapplied	Sinusoidal half wave, initial $T_J = T_J$ maximum	11 000	
		t = 8.3 ms			11 500	
		t = 10 ms	100 % V_{RRM} reapplied		9250	
		t = 8.3 ms			9700	
Maximum I^2t for fusing	I^2t	t = 10 ms	No voltage reapplied		605	kA^2s
		t = 8.3 ms			553	
		t = 10 ms	100 % V_{RRM} reapplied		428	
		t = 8.3 ms			391	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 to 10 ms, no voltage reapplied			6050	$kA^2\sqrt{s}$
Maximum peak on-state voltage	V_{TM}	I_{TM} = 1810 A, $T_J = T_J$ maximum, t_p = 10 ms sine wave pulse			1.96	V
Low level value of threshold voltage	$V_{T(TO)1}$	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ maximum			0.91	
High level value of threshold voltage	$V_{T(TO)2}$	(I > π x $I_{T(AV)}$), $T_J = T_J$ maximum			0.93	
Low level value of forward slope resistance	r_{t1}	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ maximum			0.58	mΩ
High level value of forward slope resistance	r_{t2}	(I > π x $I_{T(AV)}$), $T_J = T_J$ maximum			0.58	
Maximum holding current	I_H	T_J = 25 °C, I_T > 30 A			600	mA
Typical latching current	I_L	T_J = 25 °C, V_A = 12 V, R_a = 6 Ω, I_G = 1 A			1000	

SWITCHING

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES		UNITS
			MIN.	MAX.	
Maximum non-repetitive rate of rise of turned on current	dI/dt	$T_J = T_J$ maximum, V_{DRM} = Rated V_{DRM}; I_{TM} = 2 x dI/dt	1000		A/µs
Typical delay time	t_d	T_J = 25 °C, V_{DM} = Rated V_{DRM}, I_{TM} = 50 A DC, t_p = 1 µs Resistive load, gate pulse: 10 V, 5 Ω source	1.1		µs
Maximum turn-off time	t_q	$T_J = T_J$ maximum, I_{TM} = 550 A, commutating dI/dt = 40 A/µs V_R = 50 V, t_p = 500 µs, dV/dt: See table in device code	10	30	

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum, linear to 80 % V_{DRM}, higher value available on request	500	V/µs
Maximum peak reverse and off-state leakage current	I_{RRM}, I_{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	50	mA

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P_{GM}	$T_J = T_J$ maximum, f = 50 Hz, d% = 50	60	W
Maximum average gate power	$P_{G(AV)}$		10	
Maximum peak positive gate current	I_{GM}	$T_J = T_J$ maximum, $t_p \leq 5$ ms	10	A
Maximum peak positive gate voltage	+ V_{GM}		20	V
Maximum peak negative gate voltage	- V_{GM}		5	
Maximum DC gate currrent required to trigger	I_{GT}	T_J = 25 °C, V_A = 12 V, R_a = 6 Ω	200	mA
Maximum DC gate voltage required to trigger	V_{GT}		3	V
Maximum DC gate current not to trigger	I_{GD}	$T_J = T_J$ maximum, rated V_{DRM} applied	20	mA
Maximum DC gate voltage not to trigger	V_{GD}		0.25	V

THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum operating temperature range	T_J		- 40 to 125	°C
Maximum storage temperature range	T_{Stg}		- 40 to 150	
Maximum thermal resistance, junction to heatsink	R_{thJ-hs}	DC operation single side cooled	0.09	K/W
		DC operation double side cooled	0.04	
Maximum thermal resistance, case to heatsink	R_{thC-hs}	DC operation single side cooled	0.020	
		DC operation double side cooled	0.010	
Mounting force, ± 10 %			9800 (1000)	N (kg)
Approximate weight			83	g
Case style		See dimensions - link at the end of datasheet	TO-200AB (E-PUK)	

ΔR_{thJ-hs} CONDUCTION						
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION		RECTANGULAR CONDUCTION		TEST CONDITIONS	UNITS
	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE		
180°	0.010	0.011	0.007	0.007	$T_J = T_J$ maximum	K/W
120°	0.012	0.012	0.012	0.013		
90°	0.015	0.015	0.016	0.017		
60°	0.022	0.022	0.023	0.023		
30°	0.036	0.036	0.036	0.037		

Note

- The table above shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC

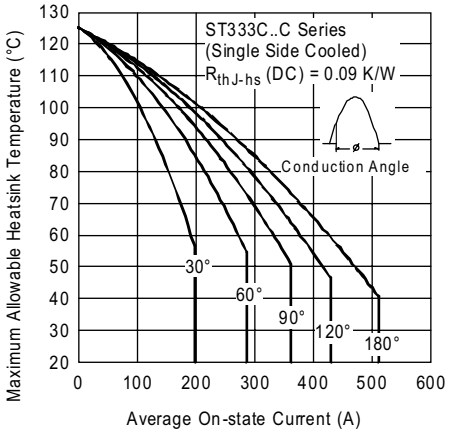


Fig. 1 - Current Ratings Characteristics

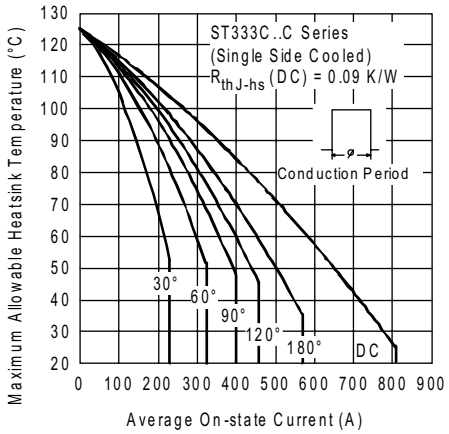


Fig. 2 - Current Ratings Characteristics

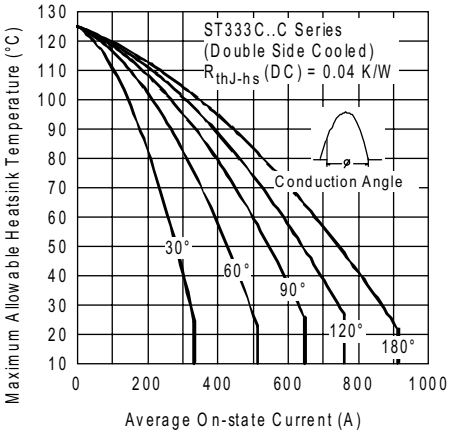


Fig. 3 - Current Ratings Characteristics

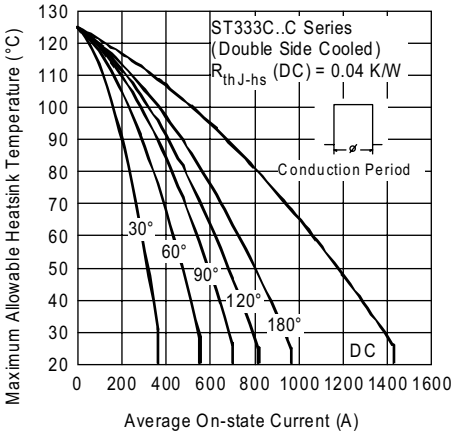


Fig. 4 - Current Ratings Characteristics

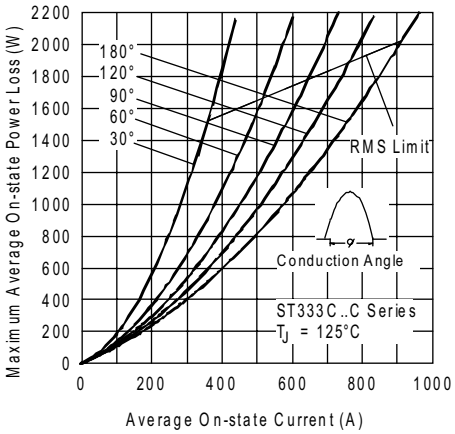


Fig. 5 - On-State Power Loss Characteristics

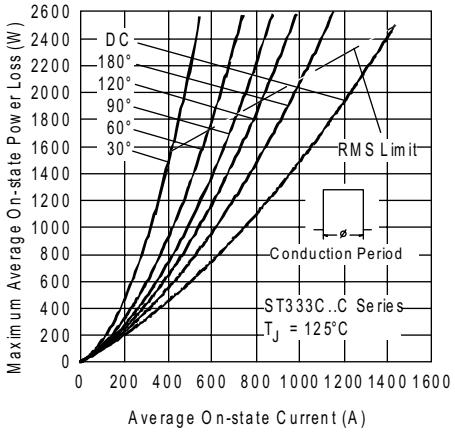


Fig. 6 - On-State Power Loss Characteristics

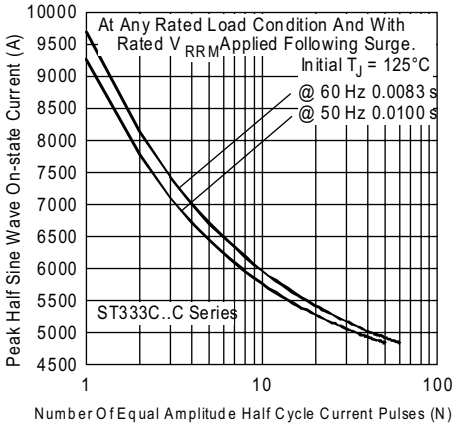


Fig. 7 - Maximum Non-Repetitive Surge Current
Single and Double Side Cooled

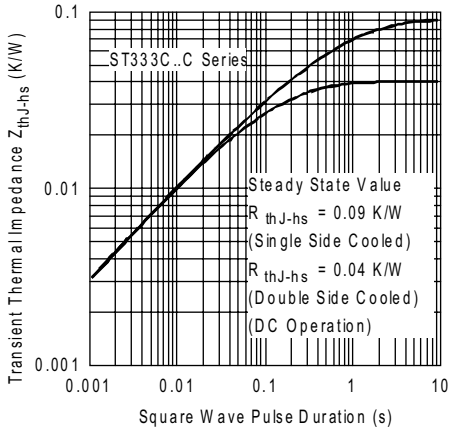


Fig. 10 - Thermal Impedance $Z_{thJ\text{-}hs}$ Characteristics

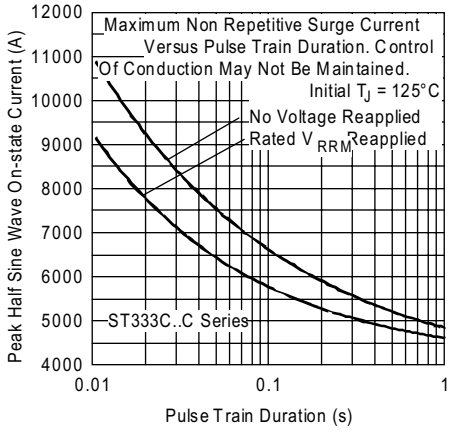


Fig. 8 - Maximum Non-Repetitive Surge Current
Single and Double Side Cooled

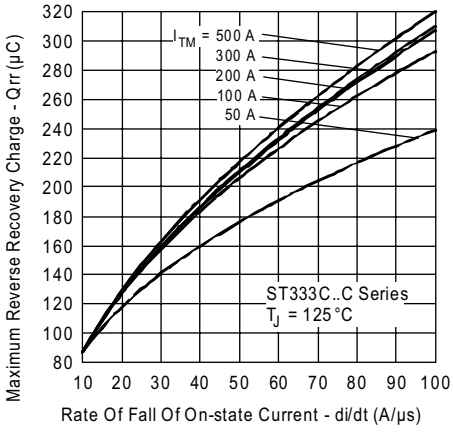


Fig. 11 - Reverse Recovered Charge Characteristics

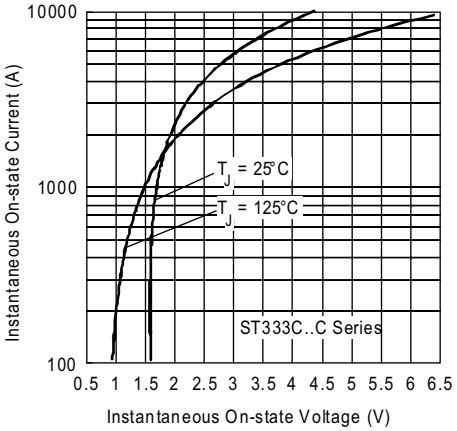


Fig. 9 - On-State Voltage Drop Characteristics

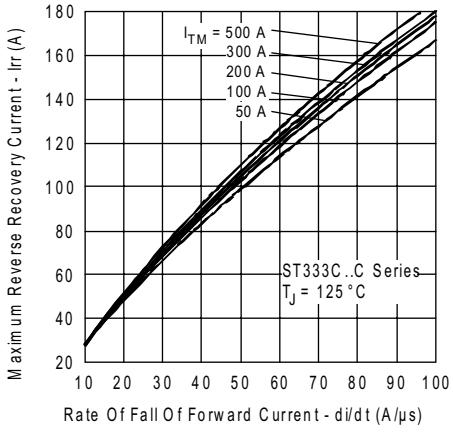


Fig. 12 - Reverse Recovery Current Characteristics

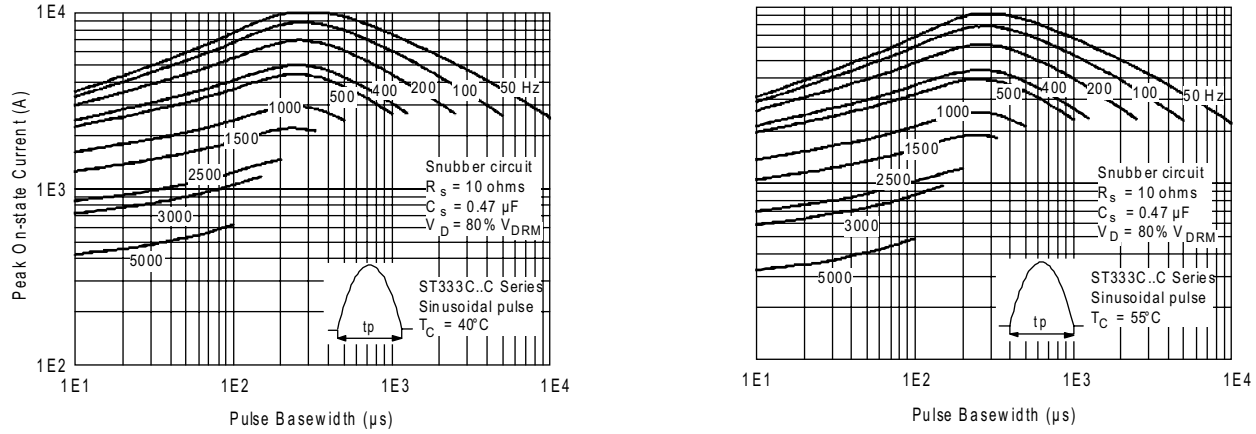


Fig. 13 - Frequency Characteristics

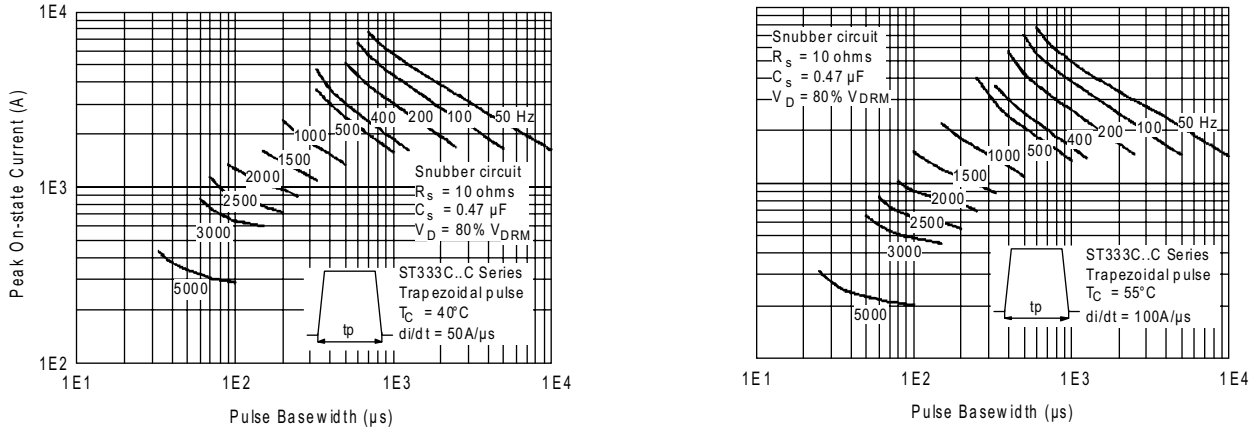


Fig. 14 - Frequency Characteristics

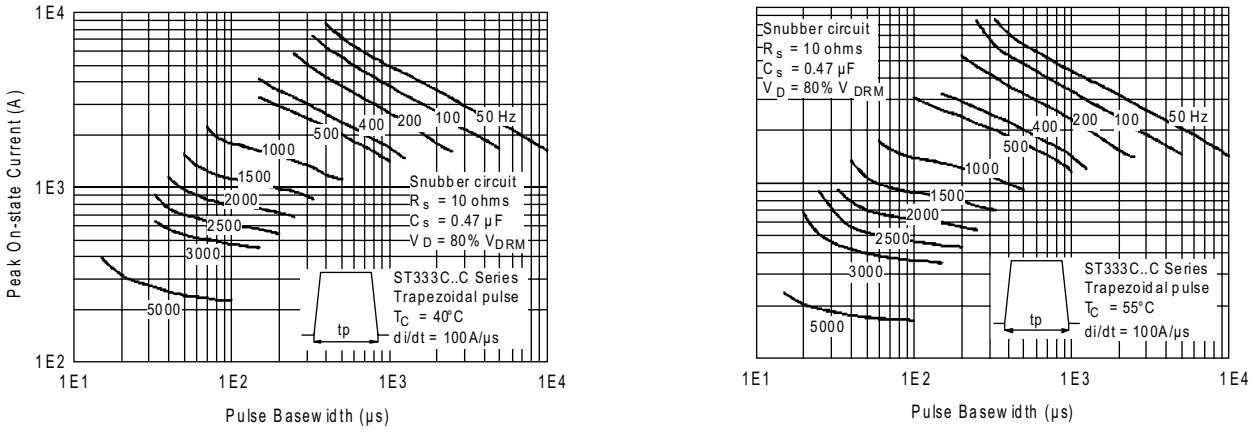


Fig. 15 - Frequency Characteristics

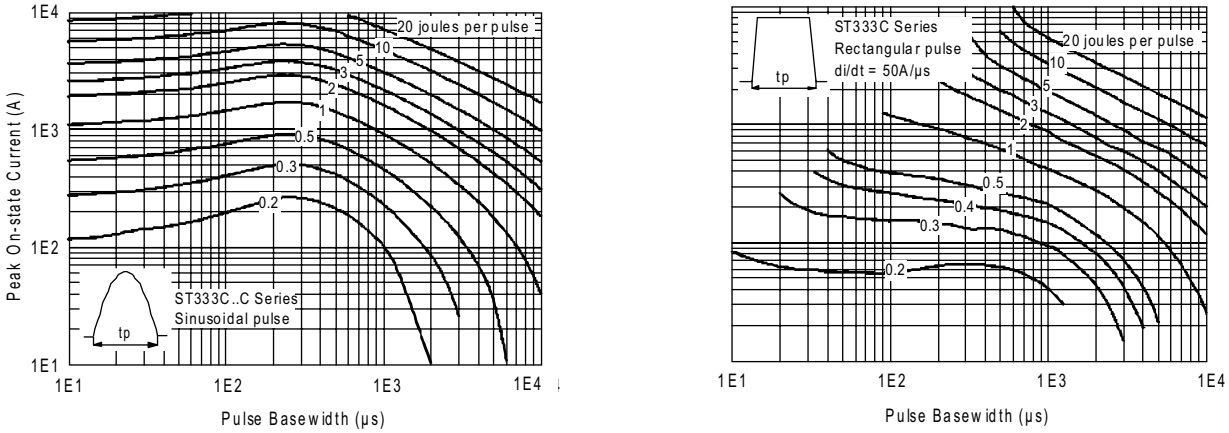


Fig. 16 - Maximum On-State Energy Power Loss Characteristics

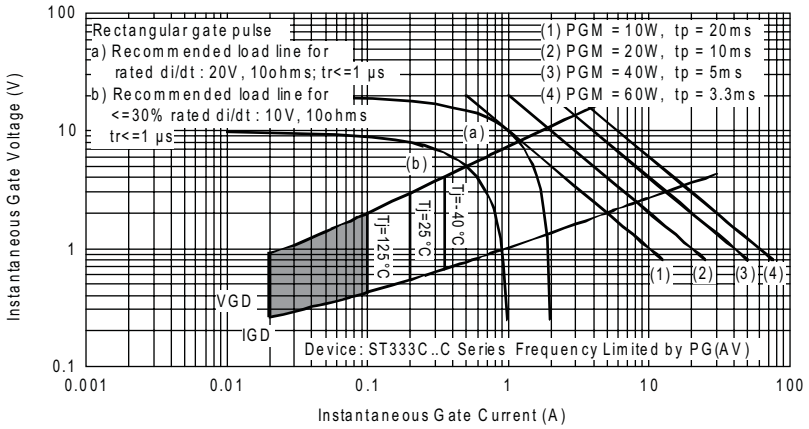


Fig. 17 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code

ST	33	3	C	08	C	H	K	1	-
1	2	3	4	5	6	7	8	9	10

1 - Thyristor

2 - Essential part number

3 - 3 = Fast turn off

4 - C = Ceramic PUK

5 - Voltage code x 100 = V_{RRM} (see Voltage Ratings table)

6 - C = PUK case TO-200AB (E-PUK)

7 - Reapplied dV/dt code (for t_q test condition)

8 - t_q code

9 - 0 = Eyelet term.
(gate and aux. cathode unsoldered leads)
1 = Fast-on term.
(gate and aux. cathode unsoldered leads)
2 = Eyelet term.
(gate and aux. cathode soldered leads)
3 = Fast-on term.
(gate and aux. cathode soldered leads)

10 - Critical dV/dt:
- None = 500 V/µs (standard value)
- L = 1000 V/µs (special selection)

dV/dt - t_q combinations available

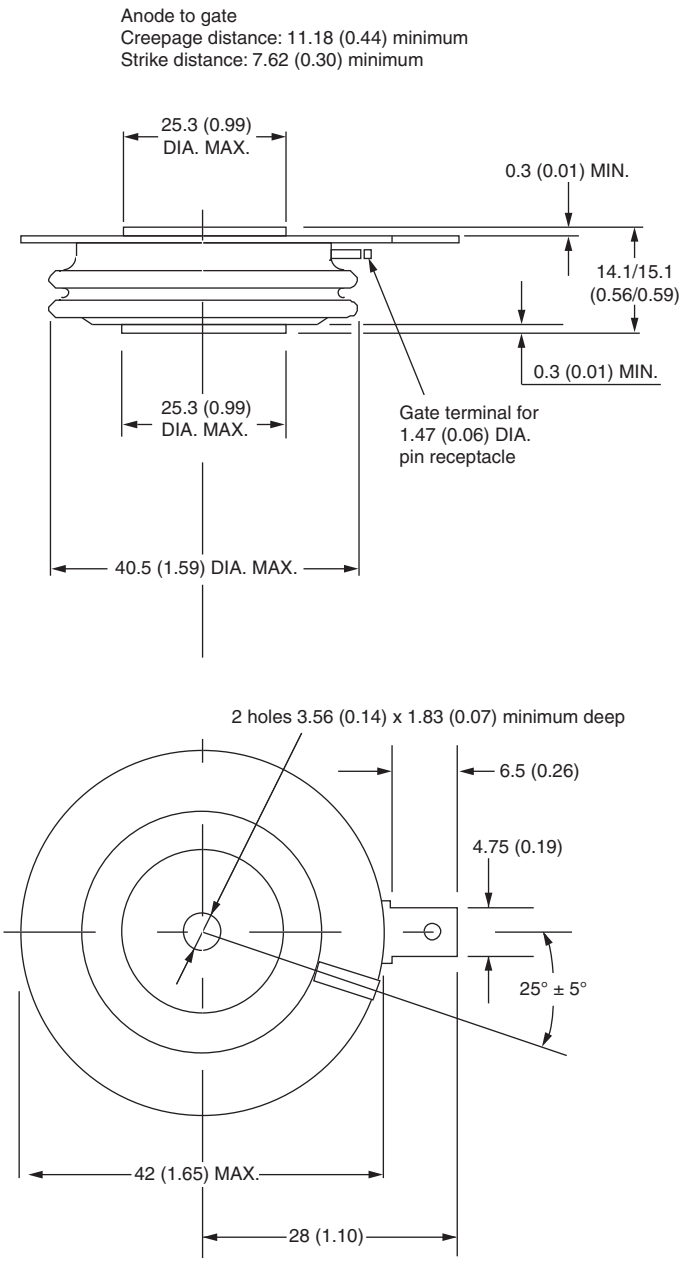
dV/dt (V/µs)	20	50	100	**200**	400
t_q (µs) 10	CN	DN	EN	--	--
12	CM	DM	EM	**FM***	--
15	CL	DL	EL	**FL***	HL
18	CP	DP	EP	FP	HP
20	CK	DK	EK	FK	HK
25	--	--	--	FJ	HJ
30	--	--	--	--	HH

* Standard part number.
All other types available only on request.

LINKS TO RELATED DOCUMENTS	
Dimensions	http://www.vishay.com/doc?95075

TO-200AB (E-PUK)

DIMENSIONS in millimeters (inches)



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, “Vishay”), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay’s knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer’s responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer’s technical experts. Product specifications do not expand or otherwise modify Vishay’s terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk and agree to fully indemnify and hold Vishay and its distributors harmless from and against any and all claims, liabilities, expenses and damages arising or resulting in connection with such use or sale, including attorneys fees, even if such claim alleges that Vishay or its distributor was negligent regarding the design or manufacture of the part. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Material Category Policy

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Vishay:
VS-ST333C04CFL0 VS-ST333C04LFL0 VS-ST333C08CFM0 VS-ST333C04CFL1 VS-ST333C04CFM1 VS-ST333C08CFL1 VS-ST333C08CFM1 VS-ST333C08LFM1 VS-ST333C08LFL0 VS-ST333C08LFL1 VS-ST333C04LFL1 VS-ST333C08CFL0 VS-ST333C04LFM1 VS-ST333C04LFM0 VS-ST333C08LFM0